

Amendments to the Claims

The listing of claims will replace all prior versions, and listings of claims in the application.

1. *(canceled)*.
2. *(previously presented)* A capacitor for an integrated circuit comprising:
a first MOS-on-NWELL (Metal Oxide Semiconductor-on-N-doped well) device formed on a substrate and having a first pickup terminal and a first gate;
a second MOS-on-NWELL device formed on the substrate and having a second pickup terminal and a second gate,
wherein the first gate is connected to the second pickup terminal, and
wherein the second gate is connected to the first pickup terminal;
a first PMOS (P-channel Metal Oxide Semiconductor) transistor formed on the substrate and having its source and drain terminals connected together; and
a second PMOS transistor formed on the substrate and having its source and drain terminals connected together,
wherein a gate of the first PMOS transistor is connected to the source and drain terminals of the second PMOS transistor,
wherein a gate of the second PMOS transistor is connected to the source and drain terminals of the first PMOS transistor,
wherein the first gate, the second pickup terminal, the gate of the first PMOS transistor and the source and drain terminals of the second PMOS transistor are connected to a first common terminal, and

wherein the second gate, the first pickup terminal, the gate of the second PMOS transistor and the source and drain terminals of the first PMOS transistor are connected to a second common terminal.

Claims 3-10. (*canceled*)